

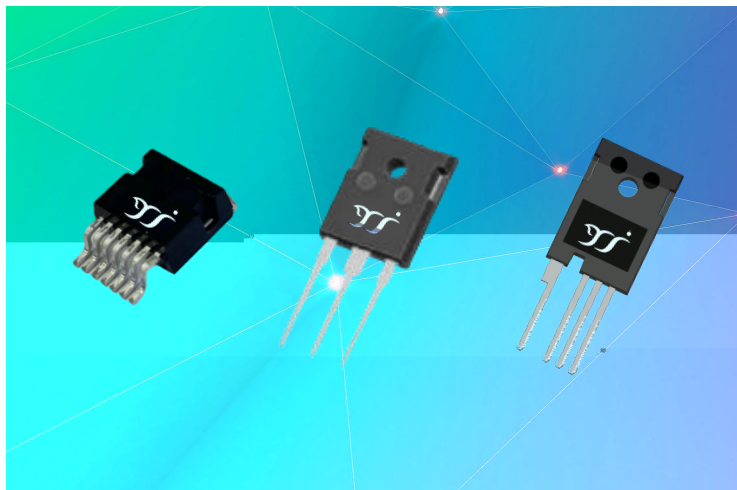
- SiC
- $Q_{rr}$
- $175^{\circ}\text{C}$

Product Name	Package	Vds(V)	ID(A)	PTOT(W)	Rdson(mohm)typ	Rdson(mohm)max	Qg(nC)typ	Vth(V)typ	Tj( )
YJD2120120B7YG3	TO-263-7L	1200	21	104	115	145	42	3.0	-55-175
YJD2120120NCFYG3	TO-247-4L		24	161					
YJD2120120NCTYG3	TO-247AB		24	161					

SiC MOSFET TO-263-7L  
 SiC MOSFET TO-247AB  
 SiC MOSFET TO-247-4L  
 1200V 120m

MOSFET





Yangjie Technology recently launched the Jie Guan self-produced 1200V 120m SiC MOSFET product, available in three packaging types: TO-247AB, TO-247-4L, and TO-263-7L. Designed for power electronics applications that demand ultimate energy efficiency and system compactness, it achieves a perfect balance between conduction loss and switching performance, specifically aimed at replacing traditional silicon-based super junction MOSFETs.

## New Product Announcement

- Leveraging the physical properties of SiC materials, this device features extremely low parasitic capacitance and very fast switching speeds. Its body diode has a very low reverse recovery charge (Qrr), which can significantly reduce switching losses, enabling power systems to easily achieve high-frequency designs and greatly enhance power density.
- It supports junction temperatures of up to 175°C. Compared to silicon devices of the same specifications, it can significantly reduce heatsink size and even allow fanless cooling in some low power density designs, reducing the overall system cost.

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Main Board



UPS



Power Supply Unit